

# HoKwon Kim

## List of Publications by Year in descending order

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22  
papers

3,436  
citations

623734

14  
h-index

752698

20  
g-index

22  
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22  
docs citations

22  
times ranked

6748  
citing authors

#	ARTICLE	IF	CITATIONS
1	Correlating chemical and electronic states from quantitative photoemission electron microscopy of transition-metal dichalcogenide heterostructures. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	2.1	5
2	Production and processing of graphene and related materials. 2D Materials, 2020, 7, 022001.	4.4	333
3	Wafer-scale MOCVD growth of monolayer MoS <sub>2</sub> on sapphire and SiO <sub>2</sub> . Nano Research, 2019, 12, 2646-2652.	10.4	104
4	Large-grain MBE-grown GaSe on GaAs with a Mexican hat-like valence band dispersion. Npj 2D Materials and Applications, 2018, 2, .	7.9	51
5	Electronic Properties of Transferable Atomically Thin MoSe <sub>2</sub> /h-BN Heterostructures Grown on Rh(111). ACS Nano, 2018, 12, 11161-11168.	14.6	17
6	Suppressing Nucleation in Metal-Organic Chemical Vapor Deposition of MoS <sub>2</sub> Monolayers by Alkali Metal Halides. Nano Letters, 2017, 17, 5056-5063.	9.1	185
7	Chemistry and electronics of single layer MoS <sub>2</sub> domains from photoelectron spectromicroscopy using laboratory excitation sources. Surface and Interface Analysis, 2016, 48, 465-469.	1.8	10
8	Free-standing electronic character of monolayer MoS <sub>2</sub> on SiO <sub>2</sub> /Si substrate by van der Waals epitaxy. Physical Review B, 2016, 94, .	1.8	10
9	Doping characteristics of iodine on as-grown chemical vapor deposited graphene on Pt. Ultramicroscopy, 2015, 159, 470-475.	1.9	3
10	Doping efficiency of single and randomly stacked bilayer graphene by iodine adsorption. Applied Physics Letters, 2014, 105, .	3.3	38
11	Epitaxial Graphene Growth and Shape Dynamics on Copper: Phase-Field Modeling and Experiments. Nano Letters, 2013, 13, 5692-5697.	9.1	142
12	Influence of Cu substrate topography on the growth morphology of chemical vapour deposited graphene. Carbon, 2013, 65, 7-12.	10.3	14
13	Optoelectronic properties of graphene thin films deposited by a Langmuir-Blodgett assembly. Nanoscale, 2013, 5, 12365.	5.6	44
14	Modeling of the self-limited growth in catalytic chemical vapor deposition of graphene. New Journal of Physics, 2013, 15, 053012.	2.9	40
15	Low-voltage graphene transistors based on self-assembled monolayer nanodielectrics. Materials Research Society Symposia Proceedings, 2012, 1451, 179-184.	0.1	0
16	Solution-processable organic dielectrics for graphene electronics. Nanotechnology, 2012, 23, 344017.	2.6	33
17	Activation Energy Paths for Graphene Nucleation and Growth on Cu. ACS Nano, 2012, 6, 3614-3623.	14.6	370
18	A review of chemical vapour deposition of graphene on copper. Journal of Materials Chemistry, 2011, 21, 3324-3334.	6.7	1,239

#	ARTICLE	IF	CITATIONS
19	Epitaxial growth in dislocation-free strained asymmetric alloy films. <i>Physical Review B</i> , 2010, 81, .	3.2	12
20	Highly Uniform 300 mm Wafer-Scale Deposition of Single and Multilayered Chemically Derived Graphene Thin Films. <i>ACS Nano</i> , 2010, 4, 524-528.	14.6	209
21	Insulator to Semimetal Transition in Graphene Oxide. <i>Journal of Physical Chemistry C</i> , 2009, 113, 15768-15771.	3.1	577
22	Large area deposition of graphene thin films by Langmuir-Blodgett assembly and their optoelectronic properties. , 2009, , .		1